

## N-Channel Enhancement Mode MOSFET

### 1. Product Information

#### 1.1 Features

- ☒ Advanced trench cell design
- ☒ Low thermal resistance
- ☒  $T_{J\max} 175^{\circ}\text{C}$
- ☒ MSL1

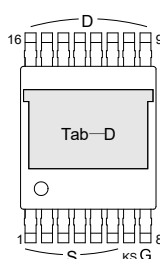
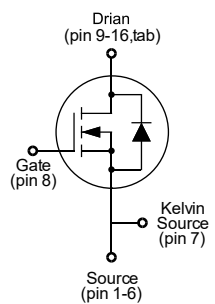
#### 1.2 Applications

- ☒ Battery management
- ☒ High power inverter system
- ☒ Uninterruptible Power Supplies
- ☒ Motor drivers

#### 1.3 Quick reference

- ☒  $BV \geq 200\text{ V}$
- ☒  $P_D \leq 429\text{ W}$
- ☒  $I_D \leq 176\text{ A}$
- ☒  $R_{DS(ON)} \leq 6\text{ m}\Omega @V_{GS} = 10\text{ V}$

### 2. Pin Description

| Pin       | Description   | Simplified Outline                                                                                   | Symbol                                                                                |
|-----------|---------------|------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------|
| 1~6       | Source        |  <p>TOLT-16L</p> |  |
| 7         | Kelvin Source |                                                                                                      |                                                                                       |
| 8         | Gate          |                                                                                                      |                                                                                       |
| 9~16, Tab | Drain         |                                                                                                      |                                                                                       |

## 3. Limiting Values

| Symbol          | Parameter                                        | Conditions                                    | Min | Max      | Unit                 |
|-----------------|--------------------------------------------------|-----------------------------------------------|-----|----------|----------------------|
| $V_{DS}$        | Drain-Source Voltage                             | $T_C=25^{\circ}\text{C}$                      | 200 | -        | V                    |
| $V_{GS}$        | Gate-Source Voltage                              | $T_C=25^{\circ}\text{C}$                      | -   | $\pm 20$ | V                    |
| $I_D$           | Drain Current (DC)                               | $T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$  | -   | 176      | A                    |
|                 |                                                  | $T_C=100^{\circ}\text{C}, V_{GS}=10\text{ V}$ | -   | 125      | A                    |
| $I_{DM}^*$      | Drain Current (Pulsed)                           | $T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$  | -   | 704      | A                    |
| $P_D$           | Drain Power Dissipation                          | $T_C=25^{\circ}\text{C}$                      | -   | 429      | W                    |
| $I_S$           | Continuous-Source Current                        | $T_C=25^{\circ}\text{C}$                      | -   | 176      | A                    |
| $E_{AS}$        | Single Pulsed Avalanche Energy                   | $V_{DD}=50\text{ V}, L=0.3\text{ mH}$         | -   | 2250     | mJ                   |
| $T_J, T_{stg}$  | Operating Junction and Storage Temperature Range |                                               | -55 | 175      | $^{\circ}\text{C}$   |
| $R_{\theta JA}$ | Thermal Resistance-Junction to Ambient           |                                               | -   | 60       | $^{\circ}\text{C/W}$ |
| $R_{\theta JC}$ | Thermal Resistance-Junction to Case              |                                               | -   | 0.5      | $^{\circ}\text{C/W}$ |

Notes:

- \* Pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- \*\* Surface mounted on 1 in<sup>2</sup> pad area,  $t \leq 10\text{ sec}$ .
- \*\*\* Limited by bonding wire.

## 4. Marking Information

| Product Name | Marking                              |
|--------------|--------------------------------------|
| KJ06N20LT1   | <b>KJ06N20LT1</b><br><b>XXXXXX-X</b> |

## 5. Ordering Code

| Product Name | Package  | Reel size | Tape width | Quantity (pcs) |
|--------------|----------|-----------|------------|----------------|
| KJ06N20LT1   | TOLT-16L | 13"       | 24 mm      | 1000           |

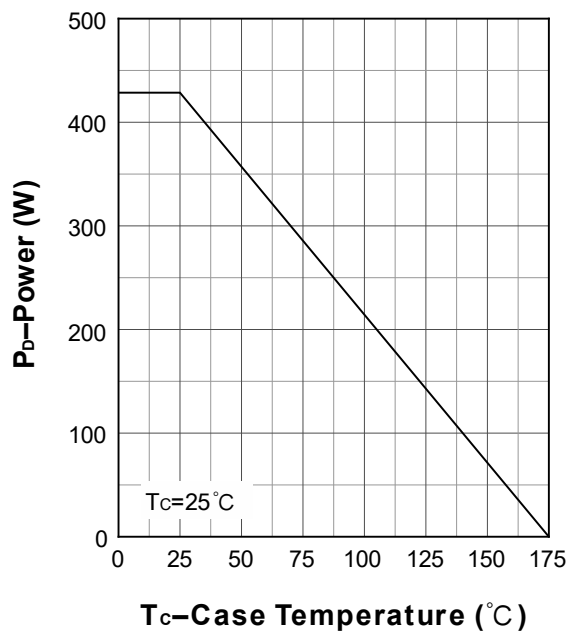
Note: KUAJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C)

## 6. Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

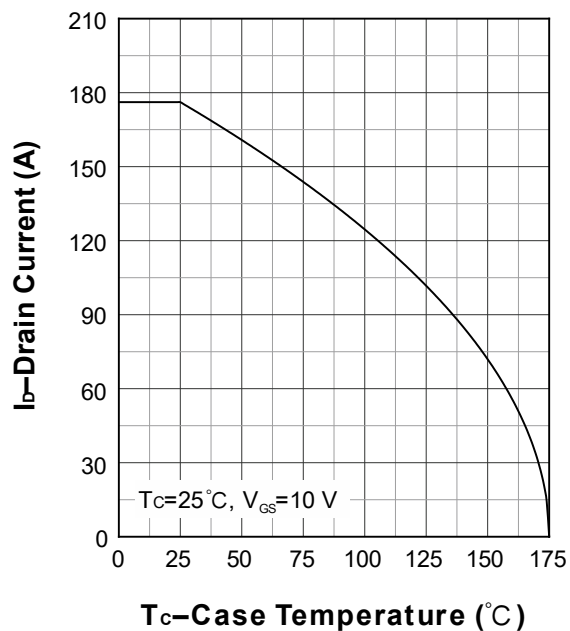
| Symbol                      | Parameter                      | Conditions                                                                                                              | Min | Typ   | Max  | Unit |
|-----------------------------|--------------------------------|-------------------------------------------------------------------------------------------------------------------------|-----|-------|------|------|
| Static Characteristics      |                                |                                                                                                                         |     |       |      |      |
| BV <sub>DSS</sub>           | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0 V, I <sub>DS</sub> =250 μA                                                                           | 200 | -     | -    | V    |
| V <sub>GS(th)</sub>         | Gate Threshold Voltage         | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250 μA                                                              | 2   | -     | 4    | V    |
| I <sub>DSS</sub>            | Drain Leakage Current          | V <sub>DS</sub> =160 V, V <sub>GS</sub> =0 V                                                                            | -   | -     | 1    | μA   |
| I <sub>GSS</sub>            | Gate Leakage Current           | V <sub>DS</sub> =0 V, V <sub>GS</sub> =±20 V                                                                            | -   | -     | ±100 | nA   |
| R <sub>DS(ON)</sub>         | On-State Resistance            | V <sub>GS</sub> =10 V, I <sub>DS</sub> =50 A                                                                            | -   | 5     | 6    | mΩ   |
| Diode Characteristics       |                                |                                                                                                                         |     |       |      |      |
| V <sub>SD</sub>             | Diode Forward Voltage          | V <sub>GS</sub> =0 V, I <sub>SD</sub> =50 A                                                                             | -   | -     | 1.3  | V    |
| t <sub>rr</sub>             | Reverse Recovery Time          | V <sub>GS</sub> =0 V, I <sub>SD</sub> =50 A,<br>dI <sub>SD</sub> /dt=100 A/μs                                           | -   | 152   | -    | ns   |
| Q <sub>rr</sub>             | Reverse Recovery Charge        |                                                                                                                         | -   | 880   | -    | nC   |
| Dynamic Characteristics     |                                |                                                                                                                         |     |       |      |      |
| C <sub>iss</sub>            | Input Capacitance              | V <sub>DS</sub> =100 V, V <sub>GS</sub> =0 V,<br>Frequency=1 MHz                                                        | -   | 11000 | -    | pF   |
| C <sub>oss</sub>            | Output Capacitance             |                                                                                                                         | -   | 910   | -    |      |
| C <sub>rss</sub>            | Reverse Transfer Capacitance   |                                                                                                                         | -   | 112   | -    |      |
| R <sub>g</sub>              | Gate Resistance                | T <sub>C</sub> =25℃                                                                                                     | -   | 1.4   | -    | Ω    |
| t <sub>d(on)</sub>          | Turn-on Delay Time             | V <sub>DS</sub> =100 V, V <sub>GEN</sub> =10 V,<br>R <sub>G</sub> =3.9 Ω, R <sub>L</sub> =2 Ω,<br>I <sub>DS</sub> =50 A | -   | 27    | -    | ns   |
| t <sub>r</sub>              | Turn-on Rise Time              |                                                                                                                         | -   | 78    | -    |      |
| t <sub>d(off)</sub>         | Turn-off Delay Time            |                                                                                                                         | -   | 148   | -    |      |
| t <sub>f</sub>              | Turn-off Fall Time             |                                                                                                                         | -   | 88    | -    |      |
| Gate Charge Characteristics |                                |                                                                                                                         |     |       |      |      |
| Q <sub>g</sub>              | Total Gate Charge              | V <sub>DS</sub> =100 V, V <sub>GS</sub> =10 V,<br>I <sub>DS</sub> =50 A                                                 | -   | 212   | -    | nC   |
| Q <sub>gs</sub>             | Gate-Source Charge             |                                                                                                                         | -   | 65    | -    |      |
| Q <sub>gd</sub>             | Gate-Drain Charge              |                                                                                                                         | -   | 40    | -    |      |

## 7. Typical Characteristics

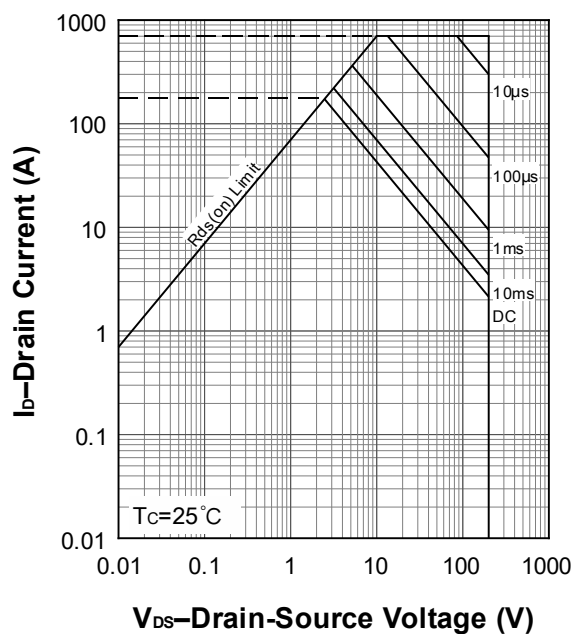
**Power Capability**



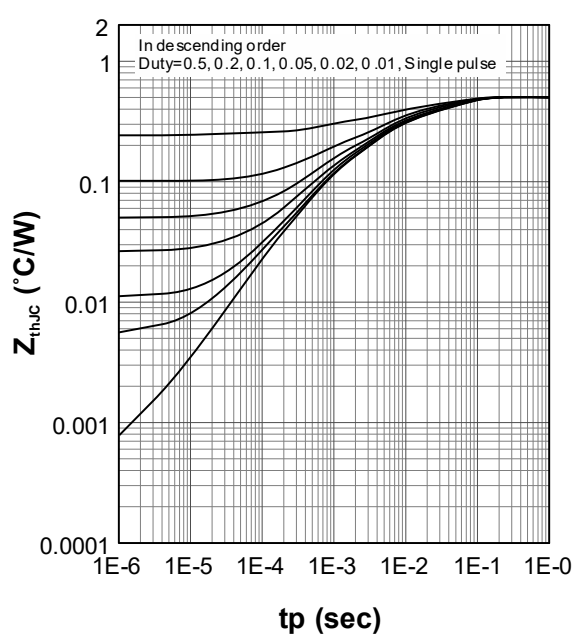
**Current Capability**



**Safe Operating Area**

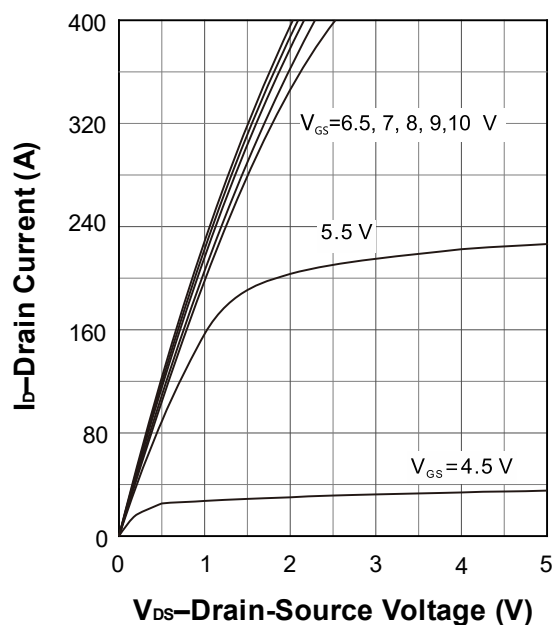


**Transient Thermal Impedance**

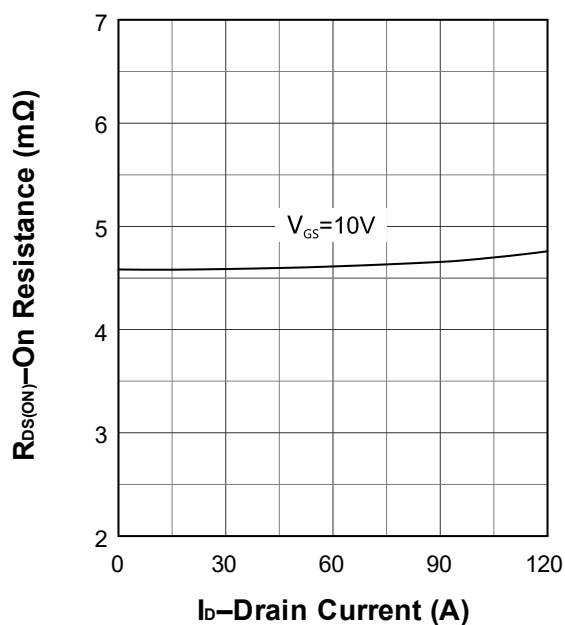


## 7. Typical Characteristics (cont.)

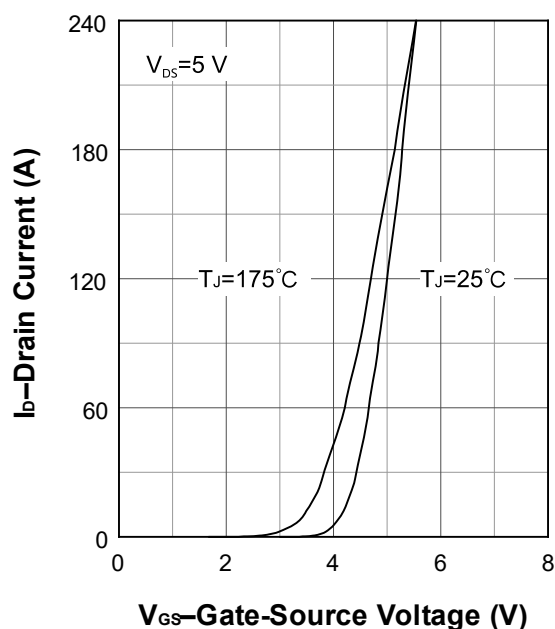
**Output Characteristics**



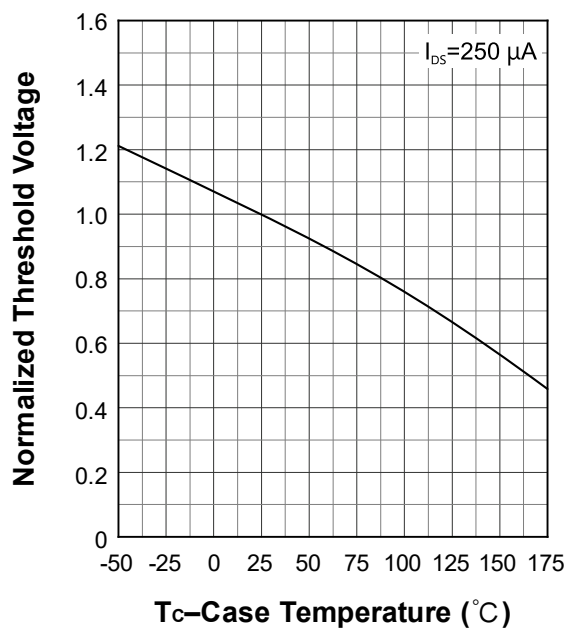
**On Resistance**



**Transfer Characteristics**

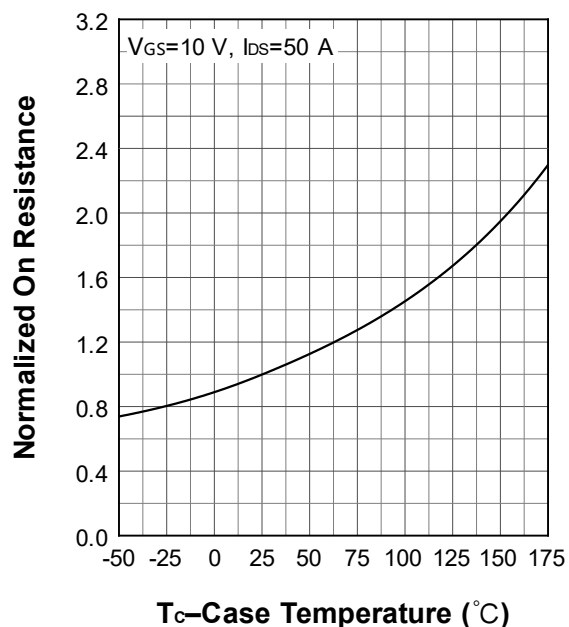


**Normalized Threshold Voltage**

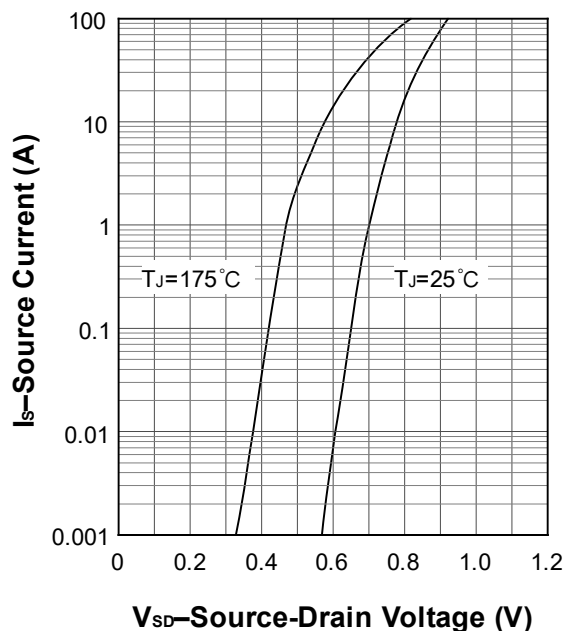


## 7. Typical Characteristics (cont.)

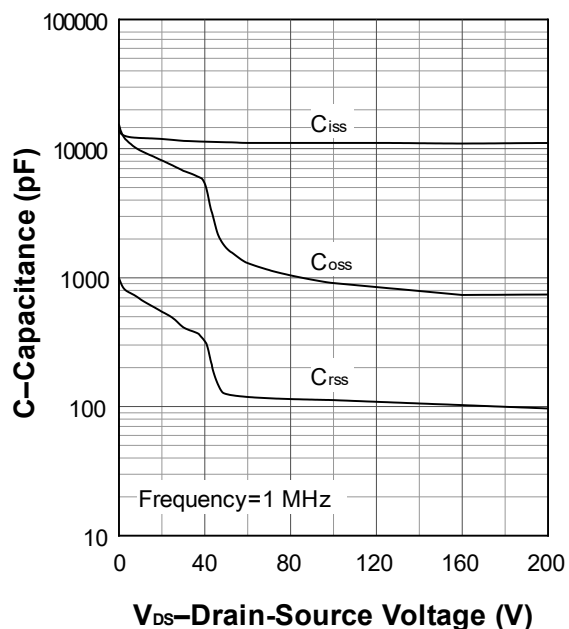
**Normalized On Resistance**



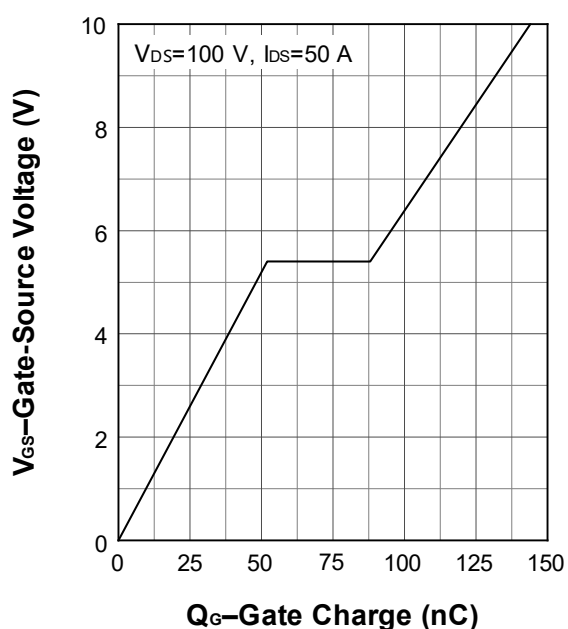
**Diode Forward Current**



**Capacitance**

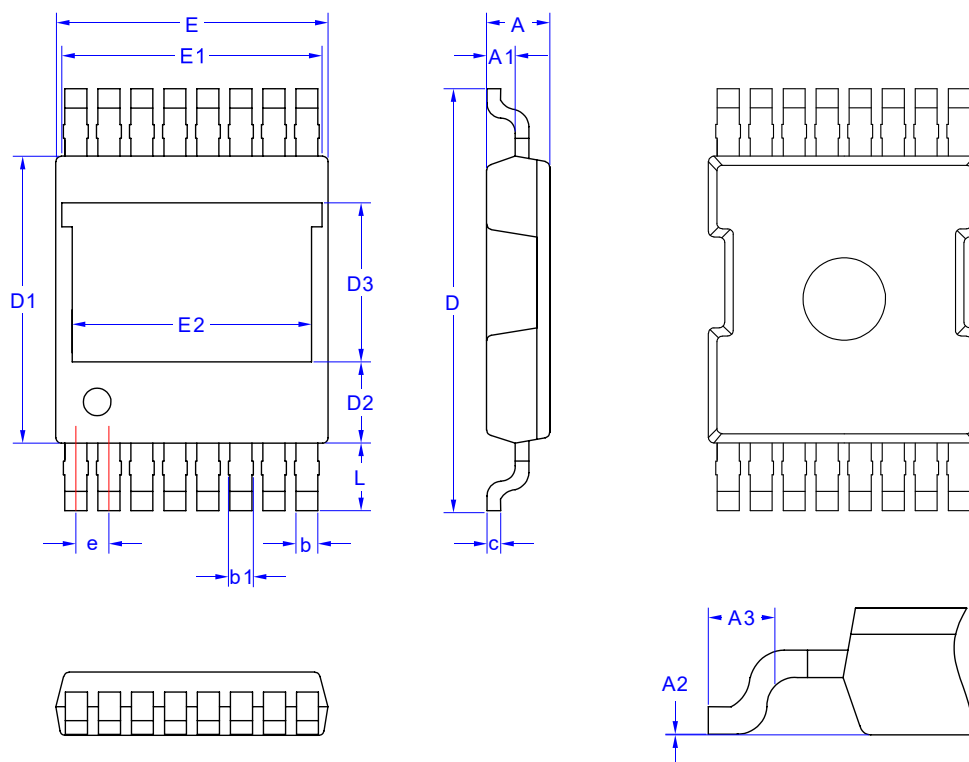


**Gate Charge**



## 8. Package Dimensions

### TOLT-16L Package



| Symbol | Dimensions in Millimeters |       |       |
|--------|---------------------------|-------|-------|
|        | MIN                       | NOM   | MAX   |
| A      | 2.20                      | 2.30  | 2.40  |
| A1     | 0.99                      | 1.04  | 1.09  |
| A2     | 0.00                      | 0.06  | 0.12  |
| A3     | 1.30 REF                  |       |       |
| b      | 0.58                      | 0.65  | 0.72  |
| c      | 0.45                      | 0.50  | 0.55  |
| D      | 14.70                     | 15.20 | 15.70 |
| D1     | 9.60                      | 10.10 | 10.60 |

| Symbol | Dimensions in Millimeters |      |       |
|--------|---------------------------|------|-------|
|        | MIN                       | NOM  | MAX   |
| D2     | 2.30                      | 2.80 | 3.30  |
| D3     | 6.20 REF                  |      |       |
| E      | 9.50                      | 9.90 | 10.30 |
| E1     | 9.00 REF                  |      |       |
| E2     | 8.20 REF                  |      |       |
| e      | 1.15                      | 1.20 | 1.25  |
| L      | 2.40                      | 2.55 | 2.70  |
|        |                           |      |       |